

INCHANGE SEMICONDUCTOR

isc N-Channel MOSFET Transistor

IXTP2R4N50P

FEATURES

- Static drain-source on-resistance: $R_{DS}(on) \le 3.75 \Omega @V_{GS}=10V$
- Fully characterized avalanche voltage and current
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATION

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

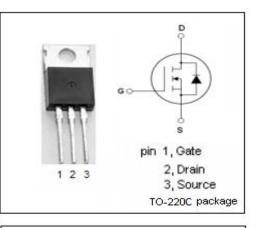
SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	500	V
V _{GS}	Gate-Source Voltage	±30	V
ID	Drain Current-Continuous	2.4	А
I _{DM}	Drain Current-Single Pulsed	4.5	А
PD	Total Dissipation @T _C =25℃	55	W
Tj	Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

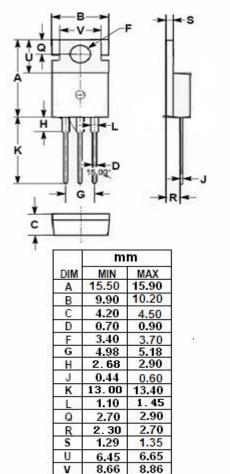
• ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th(j-c)}	Junction-to-case thermal resistance	2.27	°C/W

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ELECTRICAL CHARACTERISTICS

$T_c=25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; ID =250 μ A	500		V
$V_{GS(th)}$	Gate Threshold Voltage	V _{DS} =V _{GS} ; ID =250 μ A	3.0	5.5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} =10V; I _D = 1.2A		3.75	Ω
I _{GSS}	Gate-Source Leakage Current	V_{GS} = ±30V; V_{DS} =0V		±50	nA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = V _{DSS} ; V _{GS} = 0V		1	μ Α
		V _{DS} = V _{DSS} ; V _{GS} = 0V;T _J = 125°C		50	
V_{SD}	Diode forward voltage	I _F = 2.4A; V _{GS} = 0V		1.5	V

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